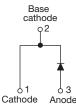
VS-HFA16TB120-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A



www.vishay.com



PRIMARY CHARACTERISTICS						
I _{F(AV)} 16 A						
V _R	1200 V					
V _F at I _F	2.3 V					
t _{rr} typ.	30 ns					
T _J max.	150 °C					
Package	2L TO-220AC					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16TB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	I _F	T _C = 100 °C	16				
Single pulse forward current	I _{FSM}		190	А			
Maximum repetitive forward current	I _{FRM}		64				
Maximum names dissinction	P _D	T _C = 25 °C	151	W			
Maximum power dissipation		T _C = 100 °C	60	vv			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			

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For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





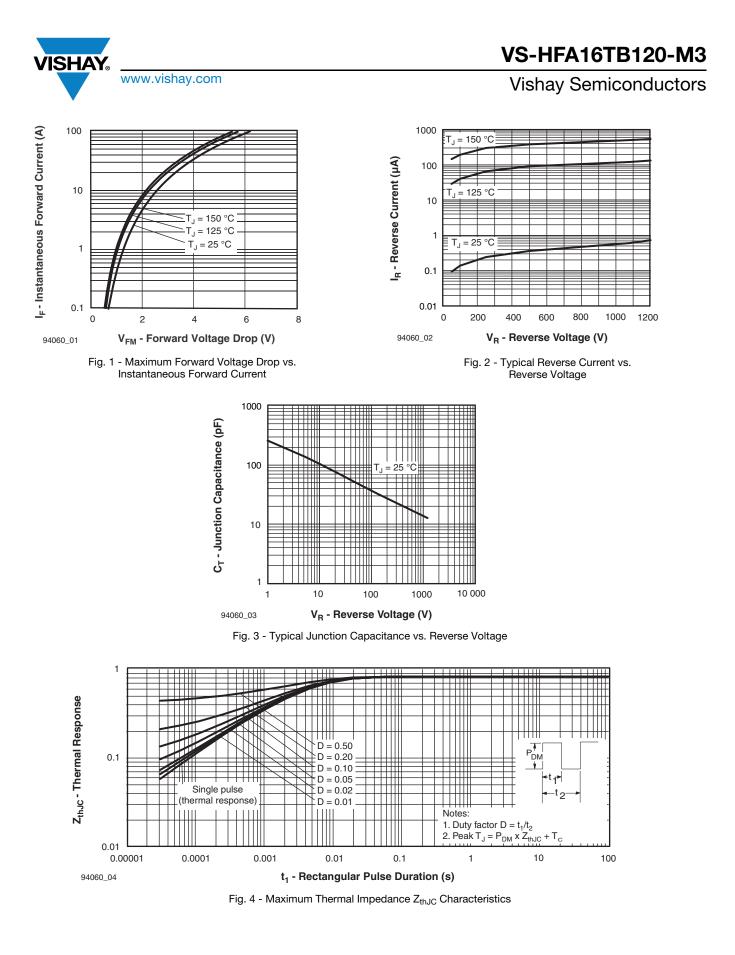
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ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-	
		I _F = 16 A		-	2.5	3.0	V
Maximum forward voltage	V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93	
	I _F = 16 A, T _J = 125 °C			-	2.3	2.7	
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 2	-	0.75	20	
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See lig. 2	-	375	2000	μA
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	ONDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	I _F = 1.0 A, di _F /dt = 200	A/μs, V _R = 30 V	-	30	-		
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	90	135	ns	
	t _{rr2}	T _J = 125 °C		-	164	245		
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 16 A	-	5.8	10	А	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15	A	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	di _F /dt = 200 A/µs V _B = 200 V	-	260	675	nC	
See fig. 7	Q _{rr2}	T _J = 125 °C	VR - 200 V	-	680	1838	nc	
Peak rate of fall of recovery current during t _b See fig. 8	di _{(rec)M} /dt1	T _J = 25 °C		-	120	-		
	di _{(rec)M} /dt2	T _J = 125 °C		-	76	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.83		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-		
Weight			-	2.0	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style 2L TO-220AC		HFA16	TB120		





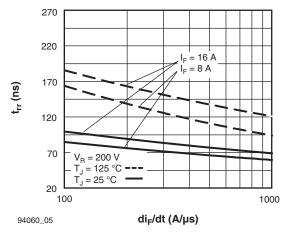


Fig. 5 - Typical Reverse Recovery Time vs. di_F/dt (Per Leg)

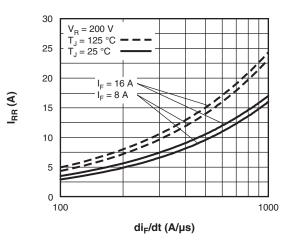


Fig. 6 - Typical Recovery Current vs. di_F/dt (Per Leg

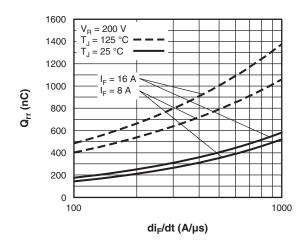


Fig. 7 - Typical Stored Charge vs. di_F/dt (Per Leg)

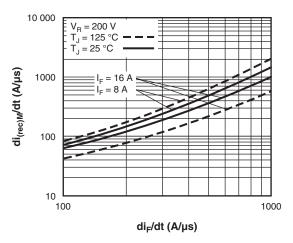


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_F/dt (Per Leg)

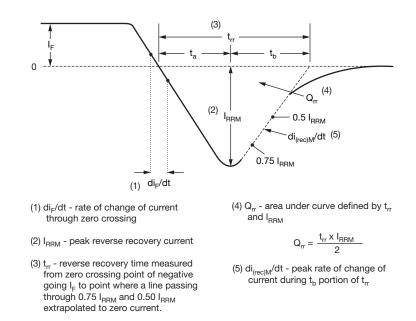


Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	A	16	тв	120	-M3
		2	3	4	5	6	7
			nay Sen KFRED [€]		ctors pro	oduct	
			ctron irra	,			
			rent rati	ng (16 =	= 16 A)		
	5		kage: = 2L TO	-220AC			
	6	- Voli	age rati	ng (120	= 1200	V)	
	7	- Env	rironmer	ntal digit	:		
		-M3	= halog	gen-free	, RoHS-	complia	ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA16TB120-M3	50	1000	Antistatic plastic tube				

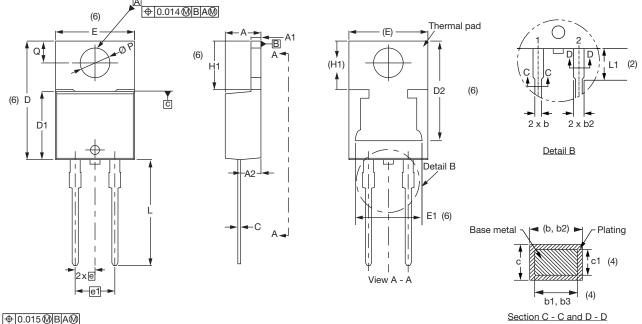
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96156			
Part marking information	www.vishay.com/doc?95391			

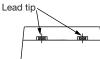


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2L TO-220AC

DIMENSIONS in millimeters and inches





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC®	outline	TO-220AC
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SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

Revision: 13-Jun-2019

1

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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